

# PRELIMINARY

Notice : This is not a final specification  
Some parametric limits are subject to change.

MITSUBISHI SEMICONDUCTOR <GaAs FET>

# MGFK39V4045

14.0~14.5GHz BAND 8W INTERNALLY MATCHD GaAs FET

## DESCRIPTION

The MGFK39V4045 is an internally impedance matched GaAs power FET especially designed for use in 14.0~14.5 GHz band amplifiers. The hermetically sealed metal-ceramic package guarantees high reliability.

## FEATURES

- Internally impedance matched
- High output power  
 $P_{1dB}=8W$  (TYP.) @ $f=14.0\sim14.5GHz$
- High linear power gain  
 $GLP=5.5dB$  (TYP.) @ $f=14.0\sim14.5GHz$
- High power added efficiency  
 $add=20\%$ (TYP.) @ $f=14.0\sim14.5GHz$ ,  $P_{1dB}$

## APPLICATION

For use in 14.0~14.5GHz band amplifiers

## QUALITY GRADE

- IG

## RECOMMENDED BIAS CONDITIONS

- $V_{DS}=10V$
- $I_D=2.4A$
- Refer to Bias Procedure

## ABSOLUTE MAXIMUM RATINGS ( $T_a=25^\circ C$ )

| Symbol    | Parameter                  | Ratings    | Unit |
|-----------|----------------------------|------------|------|
| $V_{GDO}$ | Gate to drain voltage      | -15        | V    |
| $V_{GSO}$ | Gate to source voltage     | -15        | V    |
| $I_D$     | Drain current              | 6.0        | A    |
| $I_{GR}$  | Reverse gate current       | -18        | mA   |
| $I_{GF}$  | Forward gate current       | 36         | mA   |
| $P_T$     | Total power dissipation *1 | 42.8       | W    |
| $T_{ch}$  | Channel temperature        | 175        | °C   |
| $T_{stg}$ | Storage temperature        | -65 ~ +175 | °C   |

\*1 :  $T_c=25^\circ C$

## ELECTRICAL CHARACTERISTICS ( $T_a=25^\circ C$ )

| Symbol                | Parameter                            | Test conditions                                 | Limits |      |     | Unit |
|-----------------------|--------------------------------------|-------------------------------------------------|--------|------|-----|------|
|                       |                                      |                                                 | Min.   | Typ. | Max |      |
| $I_{DSS}$             | Saturated drain current              | $V_{DS}=3V$ , $V_{GS}=0V$                       | —      | 4.0  | 6.0 | A    |
| $g_m$                 | Transconductance                     | $V_{DS}=3V$ , $I_D=2.4A$                        | 1.2    | 2.0  | —   | S    |
| $V_{GS}(\text{off})$  | Gate to source cut-off voltage       | $V_{DS}=3V$ , $I_D=20mA$                        | -2     | —    | -5  | V    |
| $P_{1dB}$             | Output power at 1dB gain compression | $V_{DS}=10V$ , $I_D=2.4A$ , $f=14.0\sim14.5GHz$ | 38.5   | 39.0 | —   | dBm  |
| $GLP$                 | Linear power gain                    |                                                 | 4.5    | 5.5  | —   | dB   |
| $add$                 | Power added efficiency               |                                                 | —      | 20   | —   | %    |
| $R_{th}(\text{ch-c})$ | Thermal resistance *1                | $V_f$ method                                    | —      | —    | 3.5 | °C/W |

\*1 : Channel to case